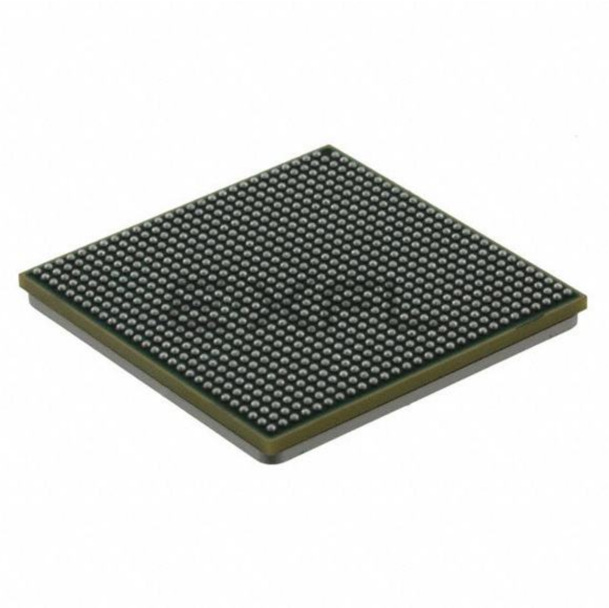

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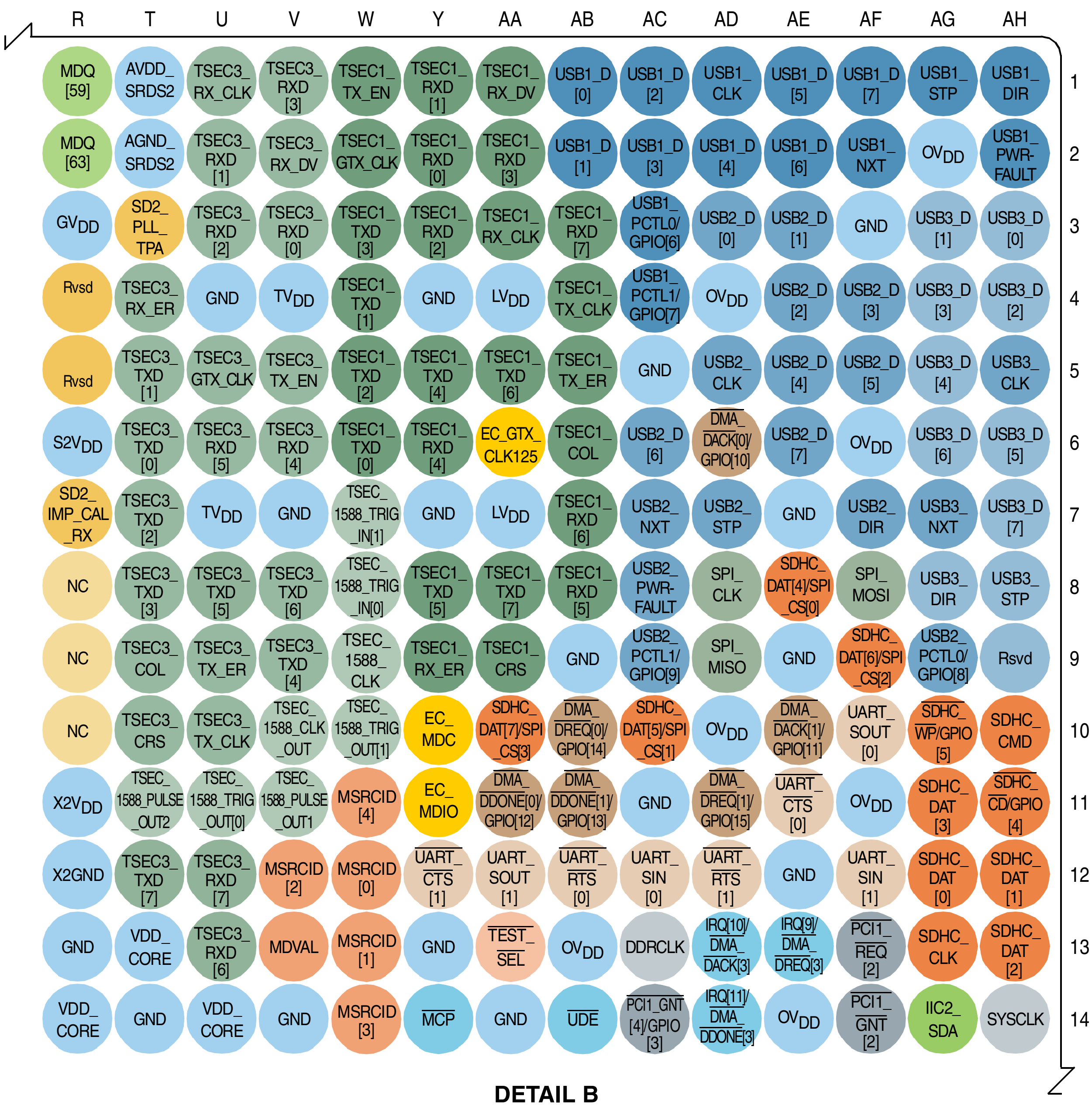
Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	800MHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR2, DDR3
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	SATA 3Gbps (1)
USB	USB 2.0 (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8535ecvtanga



DETAIL B

Figure 4. Chip Pin Map Detail B

2.1.3 Output Driver Characteristics

This table provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 4. Output Drive Capability

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
Local bus interface utilities signals	25 35	BV_{DD} = 3.3 V BV_{DD} = 2.5 V	1
	45(default) 45(default) 125	BV_{DD} = 3.3 V BV_{DD} = 2.5 V BV_{DD} = 1.8 V	
PCI signals	25	OV_{DD} = 3.3 V	2
	42 (default)		
DDR2 signal	16 32 (half strength mode)	GV_{DD} = 1.8 V	3
DDR3 signal	20 40 (half strength mode)	GV_{DD} = 1.5 V	2
TSEC signals	42	LV_{DD} = 2.5/3.3 V	—
DUART, system control, JTAG	42	OV_{DD} = 3.3 V	—
I^2C	150	OV_{DD} = 3.3 V	—

Notes:

1. The drive strength of the local bus interface is determined by the configuration of the appropriate bits in PORIMPSCR.
2. The drive strength of the PCI interface is determined by the setting of the $\overline{\text{PCI1\_GNT1}}$ signal at reset.
3. The drive strength of the DDR2 or DDR3 interface in half-strength mode is at T_j = 105°C and at GV_{DD} (min)

2.2 Power Sequencing

The chip requires its power rails to be applied in a specific sequence in order to ensure proper chip operation. These requirements are as follows for power up:

1. V_{DD_PLAT}, V_{DD_CORE} (if POWER_EN is not used to control V_{DD_CORE}), AV_{DD}, BV_{DD}, LV_{DD}, OV_{DD}, SV_{DD},$S2V_{DD}$, TV_{DD}, XV_{DD} and $X2V_{DD}$
2. [Wait for POWER_EN to assert], then V_{DD_CORE} (if POWER_EN is used to control V_{DD_CORE})
3. GV_{DD}

All supplies must be at their stable values within 50 ms.

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90% of their value before the voltage rails on the current step reach 10% of theirs.

In order to guarantee MCKE low during power-up, the above sequencing for GV_{DD} is required. If there is no concern about any of the DDR signals being in an indeterminate state during power-up, then the sequencing for GV_{DD} is not required.

From a system standpoint, if any of the I/O power supplies ramp prior to the VDD platform supply, the I/Os associated with that I/O supply may drive a logic one or zero during power-up, and extra current may be drawn by the chip.

During the Deep Sleep state, the VDD core supply is removed. But all other power supplies remain applied. Therefore, there is no requirement to apply the VDD core supply before any other power rails when the silicon waking from Deep Sleep.

Table 21. SPI AC Timing Specifications[1] (continued)

Characteristic	Symbol [2]	Min	Max	Unit	Note
SPI_CS outputs—Master data delay	$t_{NIKHOV2}$	—	6.0	ns	—
SPI inputs—Master data input setup time	t_{NIIVKH}	5	—	ns	—
SPI inputs—Master data input hold time	t_{NIIXKH}	0	—	ns	—

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOV} symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).
3. SPCOM[RxDelay] is set to 0.
4. SPCOM[RxDelay] is set to 1.

This figure provides the AC test load for the SPI.

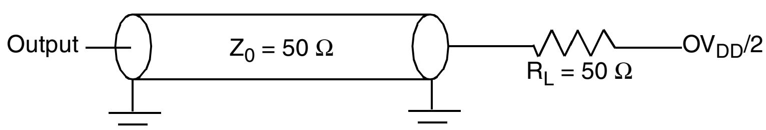


Figure 12. SPI AC Test Load

This figure represents the AC timing from Table 21. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

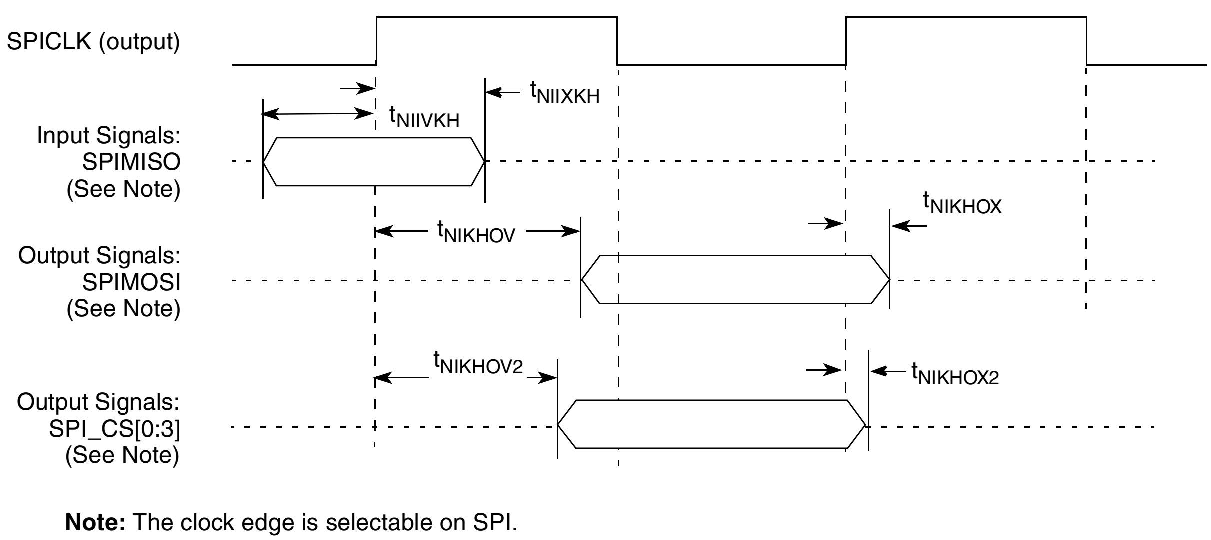


Figure 13. SPI AC Timing in Master mode (Internal Clock) Diagram

2.8 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the chip.

2.8.1 DUART DC Electrical Characteristics

This table provides the DC electrical characteristics for the DUART interface.

Table 22. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	– 0.3	0.8	V
Input current (V_{IN} [1] = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:

1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

2.8.2 DUART AC Electrical Specifications

This table provides the AC timing parameters for the DUART interface.

Table 23. DUART AC Timing Specifications

Parameter	Value	Unit	Notes
Minimum baud rate	CCB clock/1,048,576	baud	2
Maximum baud rate	CCB clock/16	baud	2,3
Oversample rate	16	—	4

Notes:

2. CCB clock refers to the platform clock.
3. Actual attainable baud rate will be limited by the latency of interrupt processing.
4. The middle of a start bit is detected as the 8^{th} sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16^{th} sample.

2.9 Ethernet: Enhanced Three-Speed Ethernet (eTSEC), MII Management

This section provides the AC and DC electrical characteristics for enhanced three-speed and MII management.

This figure shows the GMII transmit AC timing diagram.

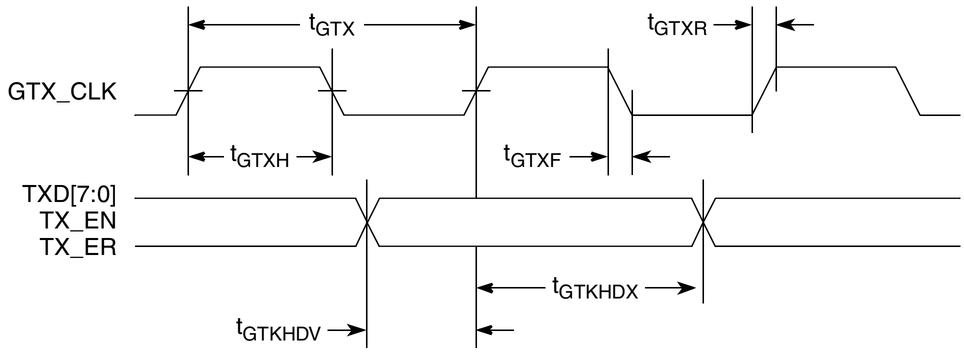


Figure 16. GMII Transmit AC Timing Diagram

2.9.2.2.2 GMII Receive AC Timing Specifications

This table provides the GMII receive AC timing specifications.

Table 29. GMII Receive AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
RX_CLK clock period	t_{GRX}	—	8.0	—	ns
RX_CLK duty cycle	t_{GRXH}/t_{GRX}	35	—	65	%
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t_{GRDVKH}	2.0	—	—	ns
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t_{GRDXKH}	0	—	—	ns
RX_CLK clock rise (20%-80%)	t_{GRXR}	—	—	1.0	ns
RX_CLK clock fall time (80%-20%)	t_{GRXF}	—	—	1.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure provides the AC test load for eTSEC.

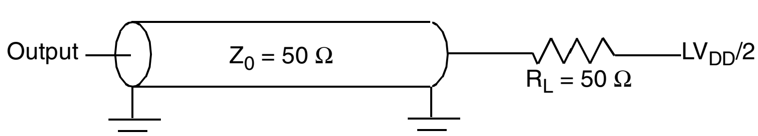


Figure 17. eTSEC AC Test Load

This figure shows the MII receive AC timing diagram.

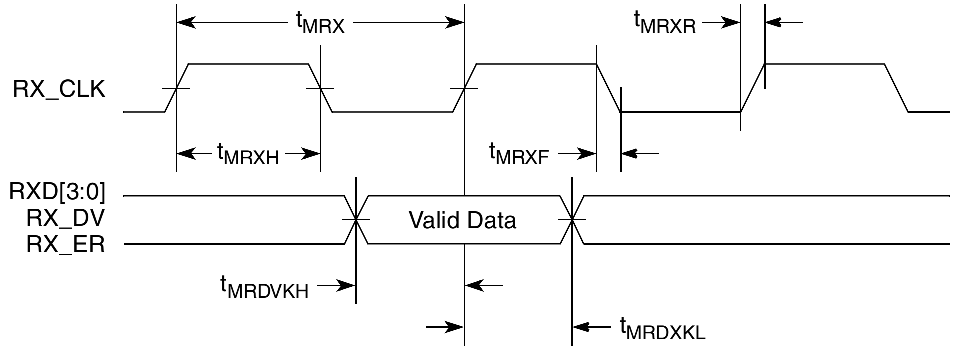


Figure 21. MII Receive AC Timing Diagram

2.9.2.4 TBI AC Timing Specifications

This section describes the TBI transmit and receive AC timing specifications.

2.9.2.4.1 TBI Transmit AC Timing Specifications

This table provides the TBI transmit AC timing specifications.

Table 32. TBI Transmit AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
GTX_CLK clock period	t_{TTX}	—	8.0	—	ns
GTX_CLK duty cycle	t_{TTXH}/t_{TTX}	40	—	60	%
GTX_CLK to TCG[9:0] delay time	t_{TTKHDX}[2]	1.0	—	5.0	ns
GTX_CLK rise (20%–80%)	t_{TTXR}	—	—	1.0	ns
GTX_CLK fall time (80%–20%)	t_{TTXF}	—	—	1.0	ns

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TTKHDV} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the valid state (V) or setup time. Also, t_{TTKHDX} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the invalid state (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TTX} represents the TBI (T) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Data valid tTTKHDV to GTX_CLK Min Setup time is a function of clock period and max hold time. (Min Setup = Cycle time - Max Hold)

This figure shows the TBI transmit AC timing diagram.

Table 36. RMII Transmit AC Timing Specifications (continued)

At recommended operating conditions with L/TV$_{DD}$ of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
Rise time TSECn_TX_CLK (20%–80%)	t_{RMTR}	1.0	—	2.0	ns
Fall time TSECn_TX_CLK (80%–20%)	t_{RMTF}	1.0	—	2.0	ns
TSECn_TX_CLK to RMII data TXD[1:0], TX_EN delay	t_{RMTDX}	2.0	—	10.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure shows the RMII transmit AC timing diagram.

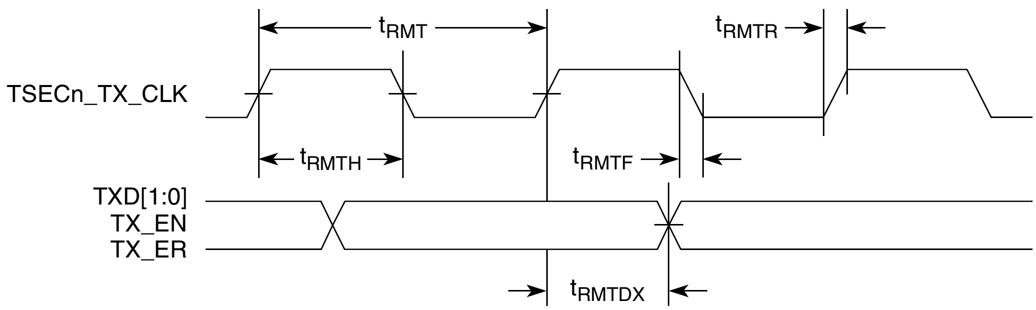


Figure 26. RMII Transmit AC Timing Diagram

2.9.2.7.2 RMII Receive AC Timing Specifications

Table 37. RMII Receive AC Timing Specifications

At recommended operating conditions with L/TV$_{DD}$ of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
TSECn_RX_CLK clock period	t_{RMR}	15.0	20.0	25.0	ns
TSECn_RX_CLK duty cycle	t_{RMRH}	35	50	65	%
TSECn_RX_CLK peak-to-peak jitter	t_{RMRJ}	—	—	250	ps
Rise time TSECn_RX_CLK (20%–80%)	t_{RMRR}	1.0	—	2.0	ns

2.9.3.4.2 SGMII Receive AC Timing Specifications

This table provides the SGMII receive AC timing specifications. Source synchronous clocking is not supported. Clock is recovered from the data. Figure 31 shows the SGMII Receiver Input Compliance Mask eye diagram.

Table 42. SGMII Receive AC Timing Specifications

At recommended operating conditions with $X2V_{DD}$ = 1.0V ± 5%.

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Deterministic Jitter Tolerance	JD	0.37	—	—	UI p-p	1
Combined Deterministic and Random Jitter Tolerance	JDR	0.55	—	—	UI p-p	1
Sinusoidal Jitter Tolerance	JSIN	0.1	—	—	UI p-p	1
Total Jitter Tolerance	JT	0.65	—	—	UI p-p	1
Bit Error Ratio	BER	—	—	10^{-12}		—
Unit Interval	UI	799.92	800	800.08	ps	2
AC Coupling Capacitor	C_{TX}	5	—	200	nF	3

Notes:
1. Measured at receiver.
2. Each UI is 800 ps ± 100 ppm.
3. The external AC coupling capacitor is required. It is recommended to be placed near the chip transmitter outputs.

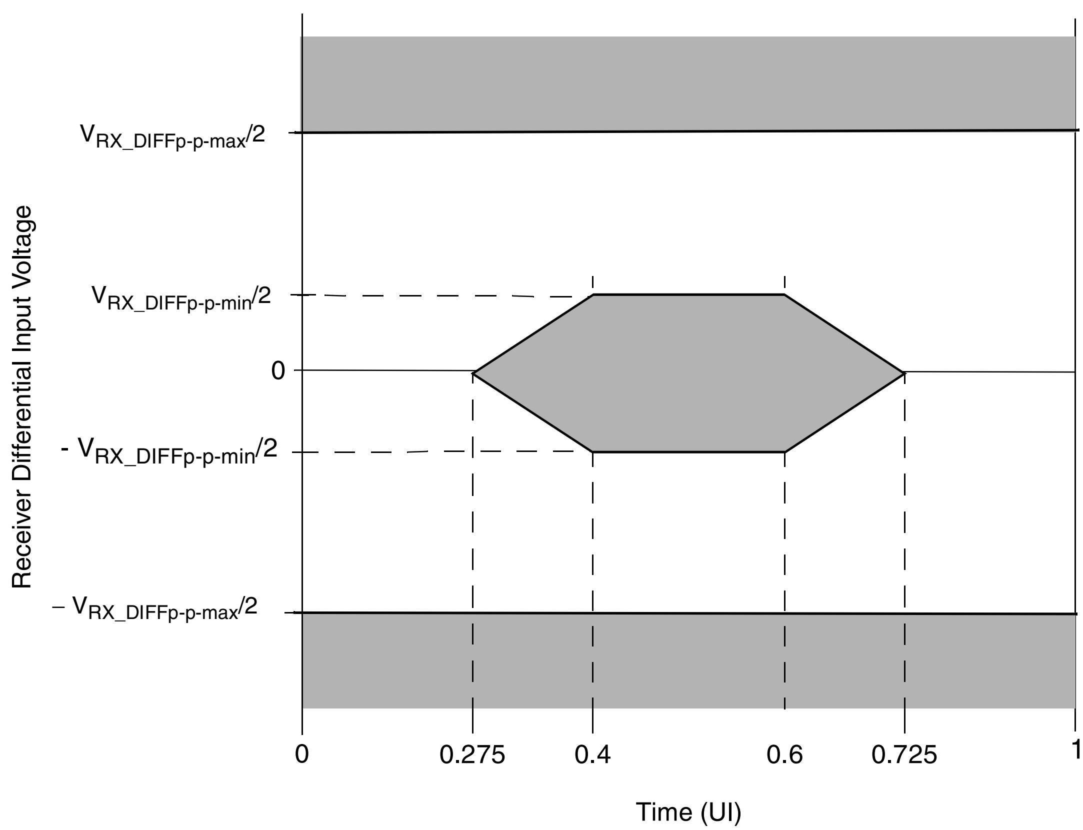


Figure 31. SGMII Receiver Input Compliance Mask

2.11.1 USB DC Electrical Characteristics

This table provides the DC electrical characteristics for the USB interface.

Table 46. USB DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current	I_{IN}	—	±5	μA
High-level output voltage, I_{OH} = –100 μA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 μA	V_{OL}	—	0.2	V

Note:

1. The symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

2.11.2 USB AC Electrical Specifications

This table describes the general timing parameters of the USB interface of the chip.

Table 47. USB General Timing Parameters[6]

Parameter	Symbol [1]	Min	Max	Unit	Notes
usb clock cycle time	t_{USCK}	15	—	ns	2-5
Input setup to usb clock - all inputs	t_{USIVKH}	4	—	ns	2-5
input hold to usb clock - all inputs	t_{USIXKH}	1	—	ns	2-5
usb clock to output valid - all outputs	t_{USKHOV}	—	7	ns	2-5
Output hold from usb clock - all outputs	t_{USKHOX}	2	—	ns	2-5

Notes:

1. The symbols for timing specifications follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{USIXKH} symbolizes usb timing (US) for the input (I) to go invalid (X) with respect to the time the usb clock reference (K) goes high (H). Also, t_{USKHOX} symbolizes USB timing (US) for the USB clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to USB clock.
3. All signals are measured from OV_{DD}/2 of the rising edge of the USB clock to 0.4 × OV_{DD} of the signal in question for 3.3 V signaling levels.
4. Input timings are measured at the pin.
5. For active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to that of the leakage current specification.
6. When switching the data pins from outputs to inputs using the USBn_DIR pin, the output timings will be violated on that cycle because the output buffers are tristated asynchronously. This should not be a problem, because the PHY should not be functionally looking at these signals on that cycle as per ULPI specifications

2.12 enhanced Local Bus Controller (eLBC)

This section describes the DC and AC electrical specifications for the local bus interface of the chip.

2.12.1 Local Bus DC Electrical Characteristics

This table provides the DC electrical characteristics for the local bus interface operating at BV_{DD} = 3.3 V DC.

Table 48. Local Bus DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
Supply voltage 3.3V	BV_{DD}	3.13	3.47	V
High-level input voltage	V_{IH}	1.9	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (BV_{IN} [1] = 0 V or BV_{IN} = BV_{DD})	I_{IN}	—	±5	μA
High-level output voltage (BV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:
1. The symbol BV_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1.

This table provides the DC electrical characteristics for the local bus interface operating at BV_{DD} = 2.5 V DC.

Table 49. Local Bus DC Electrical Characteristics (2.5 V DC)

Parameter	Symbol	Min	Max	Unit
Supply voltage 2.5V	BV_{DD}	2.37	2.63	V
High-level input voltage	V_{IH}	1.70	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.7	V
Input current (BV_{IN} [1] = 0 V or BV_{IN} = BV_{DD})	I_{IH}	—	10	μA
	I_{IL}		–15	
High-level output voltage (BV_{DD} = min, I_{OH} = –1 mA)	V_{OH}	2.0	BV_{DD} + 0.3	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 1 mA)	V_{OL}	GND – 0.3	0.4	V

Note:
1. Note that the symbol BV_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1.

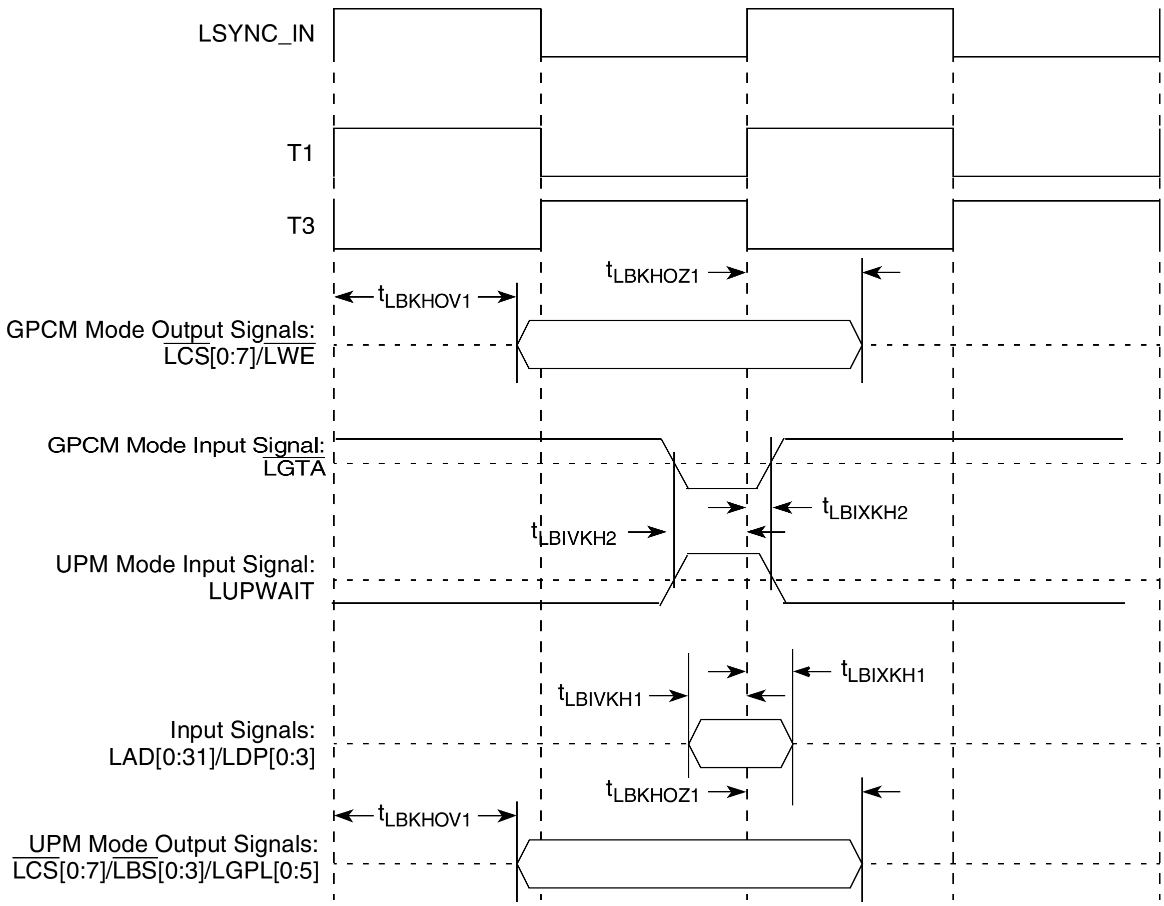


Figure 41. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4(PLL Enabled)

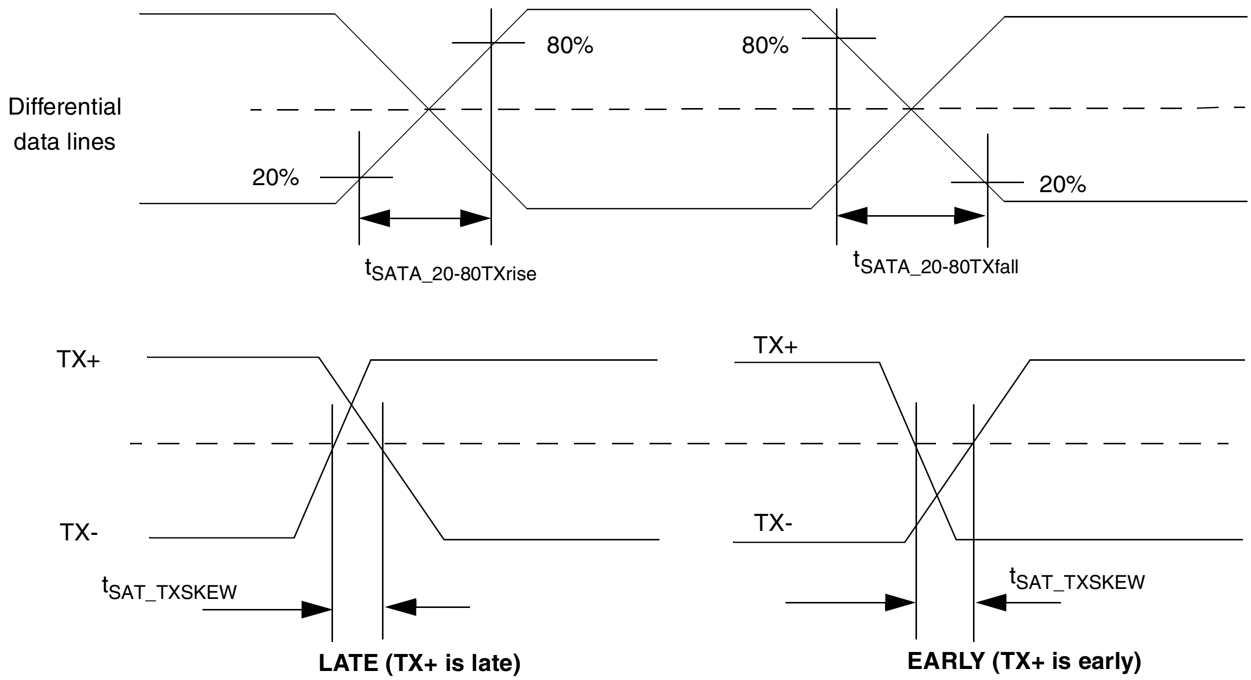


Figure 50. Signal Rise and Fall Times and Differential Skew

2.16.3 Differential Receiver (RX) Input Characteristics

This table provides the differential receiver (RX) input characteristics for the SATA interface.

Table 61. Differential Receiver (RX) Input Characteristics

Parameter	Symbol	Min	Typical	Max	Units	Notes
RX Differential Input Voltage 1.5G 3.0G	V_{SATA_RXDIFF}	240 240	400 —	600 750	mVp-p	1
RX rise/fall time 1.5G 3.0G	$t_{SATA\_20\text{-}80RX}$	100 67	— —	273 136	ps	—
RX Differential skew 1.5G 3.0G	t_{SATA_RXSKEW}	— —	— —	— 50	ps	—
RX Differential pair impedance 1.5G	$Z_{SATA\_RXDIFFIM}$	85	—	115	ohm	—
RX Single-Ended impedance 1.5G	Z_{SATA_RXSEIM}	40	—	—	ohm	—
DC Coupled Common Mode Voltage	V_{dc_cm}	200	250	450	mV	5

2.18 GPIO

This section describes the DC and AC electrical specifications for the GPIO interface of the chip.

2.18.1 GPIO DC Electrical Characteristics

This table provides the DC electrical characteristics for the GPIO interface.

Table 65. GPIO DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	– 0.3	0.8	V
Input current (V_{IN} [1] = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:

1. The symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

2.18.2 GPIO AC Electrical Specifications

This table provides the GPIO input and output AC timing specifications.

Table 66. GPIO Input and Output AC Timing Specifications[1]

Characteristic	Symbol [2]	Min	Unit	Notes
GPIO inputs—minimum pulse width	t_{PIWID}	7.5	ns	3
GPIO outputs—minimum pulse width	t_{GTOWID}	12	ns	—

Notes:

1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by any external synchronous logic. GPIO inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation.
3. The minimum pulse width is a function of the MPX/Platform clock. The minimum pulse width must be greater than or equal to 4 times the MPX/Platform clock period.

This figure provides the AC test load for the GPIO.

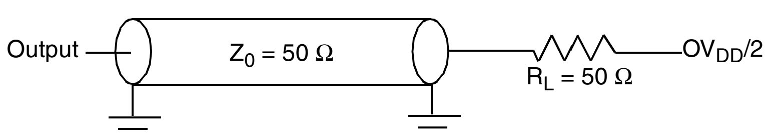


Figure 53. GPIO AC Test Load

This figure shows the PCI output AC timing conditions.

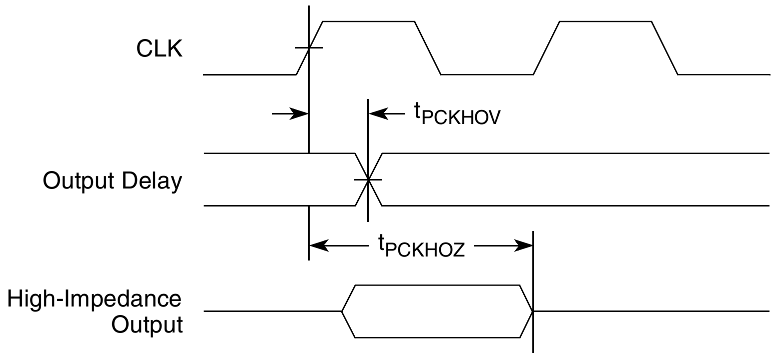


Figure 56. PCI Output AC Timing Measurement Condition

2.20 High-Speed Serial Interfaces

This chip features two Serializer/Deserializer (SerDes) interfaces to be used for high-speed serial interconnect applications. The SerDes1 interface is dedicated for PCI Express data transfers. The SerDes2 can be used for SGMII or SATA.

This section describes the common portion of SerDes DC electrical specifications, which is the DC requirement for SerDes Reference Clocks. The SerDes data lane's transmitter and receiver reference circuits are also shown.

2.20.1 Signal Terms Definition

The SerDes utilizes differential signaling to transfer data across the serial link. This section defines terms used in the description and specification of differential signals.

Figure 57 shows how the signals are defined. For illustration purposes, only one SerDes lane is used for description. The figure shows waveform for either a transmitter output (SDn_TX and $\overline{\text{SDn\_TX}}$) or a receiver input (SDn_RX and $\overline{\text{SDn\_RX}}$). Each signal swings between A Volts and B Volts where A > B.

Using this waveform, the definitions are as follows. To simplify illustration, the following definitions assume that the SerDes transmitter and receiver operate in a fully symmetrical differential signaling environment.

1. **Single-Ended Swing**

The transmitter output signals and the receiver input signals SDn_TX, $\overline{\text{SDn\_TX}}$, SDn_RX and $\overline{\text{SDn\_RX}}$ each have a peak-to-peak swing of A - B Volts. This is also referred as each signal wire's Single-Ended Swing.

2. **Differential Output Voltage, V_{OD}** (or **Differential Output Swing**):

The Differential Output Voltage (or Swing) of the transmitter, V_{OD}, is defined as the difference of the two complimentary output voltages: $V_{SDn\_TX} - V_{\overline{SDn\_TX}}$. The V_{OD} value can be either positive or negative.

3. **Differential Input Voltage, V_{ID}** (or **Differential Input Swing**):

The Differential Input Voltage (or Swing) of the receiver, V_{ID}, is defined as the difference of the two complimentary input voltages: $V_{SDn\_RX} - V_{\overline{SDn\_RX}}$. The V_{ID} value can be either positive or negative.

4. **Differential Peak Voltage**, V_{DIFFp}

The peak value of the differential transmitter output signal or the differential receiver input signal is defined as Differential Peak Voltage, $V_{DIFFp} = |A - B|$ Volts.

5. **Differential Peak-to-Peak**, $V_{DIFFp-p}$

Since the differential output signal of the transmitter and the differential input signal of the receiver each range from A - B to -(A - B) Volts, the peak-to-peak value of the differential transmitter output signal or the differential receiver input signal is defined as Differential Peak-to-Peak Voltage, $V_{DIFFp-p} = 2*V_{DIFFp} = 2 * |(A - B)|$ Volts, which is twice of differential swing in amplitude, or twice of the differential

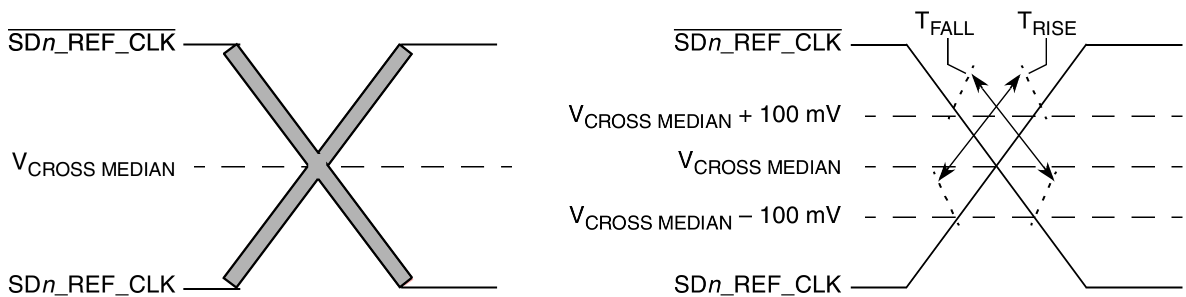


Figure 67. Single-Ended Measurement Points for Rise and Fall Time Matching

The other detailed AC requirements of the SerDes Reference Clocks is defined by each interface protocol based on application usage. See the following sections for detailed information:

- Section 2.9.3.2, "AC Requirements for SGMII SD2_REF_CLK and SD2_REF_CLK"
- Section 2.21.2, "AC Requirements for PCI Express SerDes Clocks"

2.20.2.4.1 Spread Spectrum Clock

SD1_REF_CLK/SD1_REF_CLK were designed to work with a spread spectrum clock (+0 to -0.5% spreading at 30–33 kHz rate is allowed), assuming both ends have same reference clock. For better results, a source without significant unintended modulation should be used.

SD2_REF_CLK/SD2_REF_CLK are not intended to be used with, and should not be clocked by, a spread spectrum clock source.

2.20.3 SerDes Transmitter and Receiver Reference Circuits

This figure shows the reference circuits for SerDes data lane's transmitter and receiver.

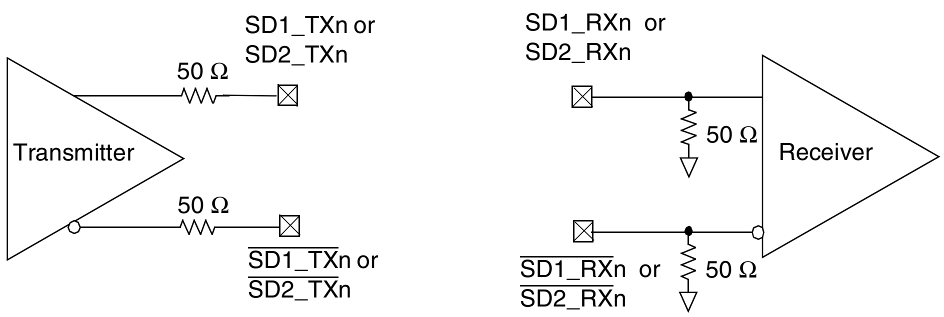


Figure 68. SerDes Transmitter and Receiver Reference Circuits

The DC and AC specification of SerDes data lanes are defined in each interface protocol section below (PCI Express, SATA or SGMII) in this document based on the application usage:

- Section 2.9.3, "SGMII Interface Electrical Characteristics"
- Section 2.21, "PCI Express"
- Section 2.16, "Serial ATA (SATA)"

Please note that external AC Coupling capacitor is required for the above three serial transmission protocols with the capacitor value defined in specification of each protocol section.

2.23.1 Clock Ranges

This table provides the clocking specifications for the processor cores and Table 74 provides the clocking specifications for the memory bus.

Table 73. Processor Core Clocking Specifications

Characteristic	Maximum Processor Core Frequency								Unit	Notes
	600 MHz		800 MHz		1000 MHz		1250 MHz			
	Min	Max	Min	Max	Min	Max	Min	Max		
e500 core processor frequency	600	600	600	800	600	1000	600	1250	MHz	1, 2
CCB frequency	400	400	400	400	333	400	333	500		
DDR Data Rate	400	400	400	400	400	400	400	500		

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. See Section 2.23.2, "CCB/SYSCLK PLL Ratio," Section 2.23.3, "e500 Core PLL Ratio,"and Section 2.23.4, "DDR/DDRCLK PLL Ratio," for ratio settings.
2. The processor core frequency speed bins listed also reflect the maximum platform (CCB) and DDR data rate frequency supported by production test. Running CCB and/or DDR data rate higher than the limit shown above, although logically possible via valid clock ratio setting in some condition, is not supported.

The DDR memory controller can run in either synchronous or asynchronous mode. When running in synchronous mode, the memory bus is clocked relative to the platform clock frequency. When running in asynchronous mode, the memory bus is clocked with its own dedicated PLL. This table provides the clocking specifications for the memory bus.

Table 74. Memory Bus Clocking Specifications

Characteristic	Maximum Processor Core Frequency		Unit	Notes
	600, 800, 1000, 1250			
	Min	Max		
DDR Memory bus clock speed	200	250	MHz	1, 2, 3, 4

Notes:

1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies. See Section 2.23.2, "CCB/SYSCLK PLL Ratio," Section 2.23.3, "e500 Core PLL Ratio," and Section 2.23.4, "DDR/DDRCLK PLL Ratio," for ratio settings.
2. The Memory bus clock refers to the chip's memory controllers' MCK[0:5] and $\overline{\text{MCK}}$[0:5] output clocks, running at half of the DDR data rate.
3. In synchronous mode, the memory bus clock speed is half the platform clock frequency. In other words, the DDR data rate is the same as the platform (CCB) frequency. If the desired DDR data rate is higher than the platform (CCB) frequency, asynchronous mode must be used.
4. In asynchronous mode, the memory bus clock speed is dictated by its own PLL. See Section 2.23.4, "DDR/DDRCLK PLL Ratio." The memory bus clock speed must be less than or equal to the CCB clock rate which in turn must be less than the DDR data rate.

2.23.2 CCB/SYSCLK PLL Ratio

The CCB clock is the clock that drives the e500 core complex bus (CCB), and is also called the platform clock. The frequency of the CCB is set using the following reset signals, as shown in the following table:

- SYSCLK input signal
- Binary value on LA[28:31] at power up

Note that there is no default for this PLL ratio; these signals must be pulled to the desired values.

Table 75. CCB Clock Ratio

Binary Value of LA[28:31] Signals	CCB:SYSCLK Ratio	Binary Value of LA[28:31] Signals	CCB:SYSCLK Ratio
0000	Reserved	1000	8:1
0001	Reserved	1001	9:1
0010	Reserved	1010	10:1
0011	3:1	1011	Reserved
0100	4:1	1100	12:1
0101	5:1	1101	Reserved
0110	6:1	1110	Reserved
0111	Reserved	1111	Reserved

2.23.3 e500 Core PLL Ratio

This table describes the clock ratio between the e500 core complex bus (CCB) and the e500 core clock. This ratio is determined by the binary value of LBCTL, LALE and LGPL2 at power up, as shown in this table.

Table 76. e500 Core to CCB Clock Ratio

Binary Value of LBCTL, LALE, LGPL2 Signals	e500 core: CCB Clock Ratio	Binary Value of LBCTL, LALE, LGPL2 Signals	e500 core: CCB Clock Ratio
000	4:1	100	2:1
001	9:2	101	5:2
010	Reserved	110	3:1
011	3:2	111	7:2

2.23.4 DDR/DDRCLK PLL Ratio

The DDR memory controller complex can be synchronous with, or asynchronous to, the CCB, depending on configuration.

The following table describes the clock ratio between the DDR memory controller complex and the DDR/DDRCLK PLL reference clock, DDRCLK, which is not the memory bus clock.

When synchronous mode is selected, the memory buses are clocked at half the CCB clock rate. The default mode of operation is for the DDR data rate for the DDR controller to be equal to the CCB clock rate in synchronous mode, or the resulting DDR PLL rate in asynchronous mode.

In asynchronous mode, the DDR PLL rate to DDRCLK ratios listed in Table 77 reflects the DDR data rate to DDRCLK ratio, since the DDR PLL rate in asynchronous mode means the DDR data rate resulting from DDR PLL output.

2.23.6 Frequency Options

2.23.6.1 SYSCLK to Platform Frequency Options

This table shows the expected frequency values for the platform frequency when using a CCB clock to SYSCLK ratio in comparison to the memory bus clock speed.

Table 78. Frequency Options of SYSCLK with Respect to Memory Bus Speeds

CCB to SYSCLK Ratio	SYSCLK (MHz)						
	33.33	41.66	66.66	83	100	111	133.33
	Platform /CCB Frequency (MHz)						
3						333	400
4				333	400	444	
5			333	415	500		
6			400	500			
8		333					
10	333	417					
12	400	500					

2.24 Thermal

This section describes the thermal specifications of the chip.

2.24.1 Thermal Characteristics

This table provides the package thermal characteristics.

Table 79. Package Thermal Characteristics

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Junction-to-ambient Natural Convection	Single layer board (1s)	$R_{\theta JA}$	23	°C/W	1, 2
Junction-to-ambient Natural Convection	Four layer board (2s2p)	$R_{\theta JA}$	18	°C/W	1, 2
Junction-to-ambient (@200 ft/min)	Single layer board (1s)	$R_{\theta JA}$	18	°C/W	1, 2

These capacitors should have a value of 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 µF (AVX TPS tantalum or Sanyo OSCON). However, customers should work directly with their power regulator vendor for best values types and quantity of bulk capacitors.

3.5 SerDes Block Power Supply Decoupling Recommendations

he SerDes1 and SerDes2 blocks require a clean, tightly regulated source of power (SnV_{DD} and XnV_{DD}) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors should be used to minimize inductance. Connections from all capacitors to power and ground should be done with multiple vias to further reduce inductance.

- First, the board should have at least 10 x 10-nF SMT ceramic chip capacitors as close as possible to the supply balls of the chip. Where the board has blind vias, these capacitors should be placed directly below the chip supply and ground connections. Where the board does not have blind vias, these capacitors should be placed in a ring around the chip as close to the supply and ground connections as possible.
- Second, there should be a 1-µF ceramic chip capacitor from each SerDes supply (SnV_{DD} and XnV_{DD}) to the board ground plane on each side of the chip. This should be done for all SerDes supplies.
- Third, between the chip and any SerDes voltage regulator there should be a 10-µF, low equivalent series resistance (ESR) SMT tantalum chip capacitor and a 100-µF, low ESR SMT tantalum chip capacitor. This should be done for all SerDes supplies.

3.6 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. All unused active low inputs should be tied to $V_{DD,}TV_{DD}$, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} as required. All unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected. Power and ground connections must be made to all external $V_{DD,}TV_{DD}$, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} and GND pins of the chip.

3.7 Pull-Up and Pull-Down Resistor Requirements

The chip requires weak pull-up resistors (2–10 kΩ is recommended) on open drain type pins including I^2C pins and MPIC interrupt pins.

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in Figure 78. Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as most have asynchronous behavior and spurious assertion will give unpredictable results.

The following pins must NOT be pulled down during power-on reset: TSEC1_TXD[3], $\overline{\text{HRESET\_REQ}}$, TRIG_OUT/READY/$\overline{\text{QUIESCE}}$, MSRCID[2:4], ASLEEP. The UART_SOUT[0:1] and $\overline{\text{TEST\_SEL}}$ pins must be set to a proper state during POR configuration. Please refer to the pinlist table (see Table 62) of the individual chip for more details.

See the PCI 2.2 specification for all pull-ups required for PCI.

3.8 Output Buffer DC Impedance

The chip drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

Careful board layout with stubless connections to these pull-down resistors coupled with the large value of the pull-down resistor should minimize the disruption of signal quality or speed for output pins thus configured.

The platform PLL ratio and e500 PLL ratio configuration pins are not equipped with these default pull-up devices.

3.10 JTAG Configuration Signals

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in Figure 78. Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as mo have asynchronous behavior and spurious assertion will give unpredicatable results.

Boundary-scan testing is enabled through the JTAG interface signals. The $\overline{TRST}$ signal is optional in the IEEE 1149.1 specification, but it is provided on all processors built on Power Architecture technology. The chip requires $\overline{TRST}$ to be asserted during power-on reset flow to ensure that the JTAG boundary logic does not interfere with normal chip operation. While the TAP controller can be forced to the reset state using only the TCK and TMS signals, generally systems assert $\overline{TRST}$ during the power-on reset flow. Simply tying $\overline{TRST}$ to $\overline{HRESET}$ is not practical because the JTAG interface is also used for accessing the common on-chip processor (COP), which implements the debug interface to the chip.

The COP function of these processors allow a remote computer system (typically, a PC with dedicated hardware and debugging software) to access and control the internal operations of the processor. The COP interface connects primarily through the JTAG port of the processor, with some additional status monitoring signals. The COP port requires the ability to independently asser $\overline{HRESET}$ or $\overline{TRST}$